Ting Wang

List of Publications by Year
in descending order

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74 papers	2,014 citations	331259 21 h-index	233125 45 g-index
74 all docs	74 docs citations	74 times ranked	1783 citing authors

#	Article	IF	Citations
1	Long-wavelength InAs/GaAs quantum-dot laser diode monolithically grown on Ge substrate. Nature Photonics, 2011, 5, 416-419.	15.6	344
2	13-Î¼m InAs/GaAs quantum-dot lasers monolithically grown on Si substrates. Optics Express, 2011, 19, 11381.	1.7	236
3	A germanium hole spin qubit. Nature Communications, 2018, 9, 3902.	5.8	170
4	Systematic z-scan measurements of the third order nonlinearity of chalcogenide glasses. Optical Materials Express, 2014, 4, 1011.	1.6	160
5	Supercontinuum generation in bandgap engineered, backâ€end CMOS compatible silicon rich nitride waveguides. Laser and Photonics Reviews, 2015, 9, 498-506.	4.4	115
6	Multi-photon absorption and third-order nonlinearity in silicon at mid-infrared wavelengths. Optics Express, 2013, 21, 32192.	1.7	103
7	Exploring High Refractive Index Silicon-Rich Nitride Films by Low-Temperature Inductively Coupled Plasma Chemical Vapor Deposition and Applications for Integrated Waveguides. ACS Applied Materials & Interfaces, 2015, 7, 21884-21889.	4.0	74
8	Ultrafast coherent control of a hole spin qubit in a germanium quantum dot. Nature Communications, 2022, 13, 206.	5.8	58
9	Enhanced optical Kerr nonlinearity of graphene/Si hybrid waveguide. Applied Physics Letters, 2019, 114, .	1.5	50
10	InAs QDs on (111)-faceted Si (001) hollow substrates with strong emission at 1300â€‰nm and 1550â€‰nm. Applied Physics Letters, 2018, 113, .	1.5	48
11	Wavelength selective mode division multiplexing on a silicon chip. Optics Express, 2015, 23, 8095.	1.7	40
12	Siteâ€Controlled Uniform Ge/Si Hut Wires with Electrically Tunable Spinâ€“Orbit Coupling. Advanced Materials, 2020, 32, e1906523.	11.1	40
13	Quasiphase matched harmonic generation in a two-dimensional octagonal photonic superlattice. Applied Physics Letters, 2005, 87, 251103.	1.5	37
14	Coupling a Germanium Hut Wire Hole Quantum Dot to a Superconducting Microwave Resonator. Nano Letters, 2018, 18, 2091-2097.	4.5	36
15	InAs/GaAs quantum dot narrow ridge lasers epitaxially grown on SOI substrates for silicon photonic integration. Optics Express, 2020, 28, 26555.	1.7	32
16	1300 nm Wavelength InAs Quantum Dot Photodetector Grown on Silicon. Optics Express, 2012, 20, 10446.	1.7	31
17	InAs/GaAs quantum dot single-section mode-locked lasers on Si (001) with optical self-injection feedback. Optics Express, 2021, 29, 674.	1.7	27
18	Second and third order dispersion generation using nonlinearly chirped silicon waveguide gratings. Optics Express, 2013, 21, 29223.	1.7	26

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19	O-Band and C/L-Band III-V Quantum Dot Lasers Monolithically Grown on Ge and Si Substrate. Applied Sciences (Switzerland), 2019, 9, 385.	1.3	26
20	Ultracompact Fiber-to-Chip Metamaterial Edge Coupler. ACS Photonics, 2021, 8, 3226-3233.	3.2	22
21	Ultra-broadband flat-top quantum dot comb lasers. Photonics Research, 2022, 10, 1308.	3.4	22
22	Anisotropy of domain broadening in periodically poled lithium niobate crystals. Applied Physics Letters, 2006, 88, 041121.	1.5	21
23	Phosphorus-free 1.5â€‰â€‰Âµm InAs quantum-dot microdisk lasers on metamorphic InGaAs/SOI platform. Optics Letters, 2020, 45, 2042.	1.7	21
24	Measuring hole spin states of single quantum dot in germanium hut wire. Applied Physics Letters, 2017, 110, .	1.5	19
25	1310 nm InAs quantum-dot microdisk lasers on SOI by hybrid epitaxy. Optics Express, 2019, 27, 19348.	1.7	18
26	Position-dependent chiral coupling between single quantum dots and cross waveguides. Applied Physics Letters, 2021, 118, .	1.5	17
27	Perspective: optically-pumped IIIâ€“V quantum dot microcavity lasers via CMOS compatible patterned Si (001) substrates. Journal of Semiconductors, 2019, 40, 101303.	2.0	16
28	Anisotropic g-Factor and Spinâ€“Orbit Field in a Germanium Hut Wire Double Quantum Dot. Nano Letters, 2021, 21, 3835-3842.	4.5	16
29	Gate-Tunable Spin-Orbit Coupling in a Germanium Hole Double Quantum Dot. Physical Review Applied, 2022, 17, .	1.5	15
30	O-band InAs/GaAs quantum-dot microcavity laser on Si (001) hollow substrate by in-situ hybrid epitaxy. AIP Advances, 2019, 9, 015331.	0.6	14
31	Dipole coupling of a hole double quantum dot in germanium hut wire to a microwave resonator. New Journal of Physics, 2020, 22, 083068.	1.2	14
32	Multi-wavelength injection locked semiconductor comb laser. Photonics Research, 2022, 10, 1840.	3.4	13
33	C/L-band emission of InAs QDs monolithically grown on Ge substrate. Optical Materials Express, 2017, 7, 2955.	1.6	12
34	On-Chip Integration of Energy-Tunable Quantum Dot Based Single-Photon Sources via Strain Tuning of GaAs Waveguides. ACS Photonics, 2020, 7, 2723-2730.	3.2	12
35	Zero Field Splitting of Heavy-Hole States in Quantum Dots. Nano Letters, 2020, 20, 5201-5206.	4.5	12
36	A CMOS Compatible Si Template with (111) Facets for Direct Epitaxial Growth of IIIâ€“V Materials*. Chinese Physics Letters, 2020, 37, 024203.	1.3	11

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37	Hybrid Integration of Deterministic Quantum Dotâ€Based Singleâ€Photon Sources with CMOSâ€Compatible Silicon Carbide Photonics. Laser and Photonics Reviews, 2022, 16, .	4.4	11
38	Hole spin in tunable Ge hut wire double quantum dot. Applied Physics Express, 2020, 13, 065002.	1.1	9
39	Sole Excited-State InAs Quantum Dot Laser on Silicon With Strong Feedback Resistance. Frontiers in Materials, 2021, 8, .	1.2	8
40	Chiral Photonic Circuits for Deterministic Spin Transfer. Laser and Photonics Reviews, 2021, 15, 2100009.	4.4	8
41	P-doped 1300â€‰â€‰nm InAs/GaAs quantum dot lasers directly grown on an SOI substrate. Optics Letters, 2021, 46, 5525.	1.7	8
42	Multi-wavelength 128 Gbit s^{â^'1} Î» ^{â^'1} PAM4 optical transmission enabled by a 100 GHz quantum dot mode-locked optical frequency comb. Journal Physics D: Applied Physics, 2022, 55, 144001.	1.3	8
43	Quantum dot lasers on silicon substrate for silicon photonic integration and their prospect. Wuli Xuebao/Acta Physica Sinica, 2015, 64, 204209.	0.2	7
44	Epitaxial growth of InAs/GaAs quantum dots on {113}-faceted Ge/Si (001) hollow substrate. Optical Materials Express, 2020, 10, 1045.	1.6	6
45	Temperature-Dependent Photoluminescence Characteristics of InAs/GaAs Quantum Dots Directly Grown on Si Substrates. Chinese Physics Letters, 2016, 33, 044207.	1.3	4
46	Kerr nonlinearity induced four-wave mixing of CMOS-compatible PECVD deposited ultra-Si-rich-nitride. Journal of Applied Physics, 2020, 128, 013102.	1.1	4
47	Measuring the complex admittance and tunneling rate of a germanium hut wire hole quantum dot. Journal of Applied Physics, 2018, 123, 174305.	1.1	3
48	Bufferless Epitaxial Growth of GaAs on Step-Free Ge (001) Mesa. Chinese Physics Letters, 2021, 38, 068101.	1.3	3
49	Suspended AlGaAs waveguide for integrated nonlinear photonics. Applied Physics Letters, 2021, 119, .	1.5	3
50	Controllable growth of GeSi nanowires on trench patterned Si(001) substrate. Wuli Xuebao/Acta Physica Sinica, 2020, 69, 028102.	0.2	3
51	Catalyst-free growth of lateral InAs nanowires. Journal of Crystal Growth, 2018, 498, 209-213.	0.7	1
52	1.3-um InAs/GaAs quantum-dot lasers monolithically grown on Ge substrate. , 2011, , .		0
53	Enhanced optical Kerr nonlinearity of graphene/Si hybrid waveguide. , 2018, , .		0
54	InAs QDs on (111)-faceted Si (001) hollow substrates with strong emission at 1300 nm and 1550 nm. , 2018, , .		0

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55	Optically pumped low threshold InAs/GaAs quantum-dot micropillar laser on Si (001) hollow substrate. , 2018, , .		0
56	InAs QDs Monolithically Grown on COMS Compatible Si (001) and SOI Platform with Strong Emission at 1300 nm and 1550 nm. , 2019, , .		0
57	Optical Kerr Nonlinearity of CMOS Compatible PECVD Deposited Si-Rich-Nitride (SRN). , 2019, , .		0
58	InAs QDs Monolithically Grown on COMS Compatible Si (001) and SOI Platform with Strong Emission at 1300 nm and 1550 nm. , 2019, , .		0
59	Spectral Broadening Enhancement in Graphene Integrated Si Waveguides. , 2019, , .		0
60	Optical Kerr Nonlinearity of CMOS Compatible PECVD Deposited Si-Rich-Nitride (SRN). , 2019, , .		0
61	Nanowires: Siteâ€Controlled Uniform Ge/Si Hut Wires with Electrically Tunable Spinâ€“Orbit Coupling (Adv. Mater. 16/2020). Advanced Materials, 2020, 32, 2070122.	11.1	0
62	Epitaxial Growth of Ordered In-Plane Si and Ge Nanowires on Si (001). Nanomaterials, 2021, 11, 788.	1.9	0
63	Magnetic transport measurements of spin-orbit and hyperfine interactions in a Ge hut wire double quantum dot. Applied Physics Express, 0, , .	1.1	0
64	IIIâ€“V quantum-dot laser growth on silicon and germanium. , 2013, , .		0
65	Optical nonlinearity in silicon at mid-infrared wavelengths. , 2014, , .		0
66	Ultra-silicon-rich nitride devices for CMOS nonlinear optics. SPIE Newsroom, 0, , .	0.1	0
67	C/L-band emission of InAs QDs monolithically grown on Ge platform. , 2017, , .		0
68	C/L-band InAs QDs on CMOS compatible Ge and on- axis Si (001) platform. , 2018, , .		0
69	Enhanced Self-Phase Modulation in Graphene-integrated Silicon Waveguides. , 2018, , .		0
70	O-band and C/L-band emission of InAs QDs monolithically grown on Ge and U-shape Si (001) platform. , 2018, , .		0
71	High gain optical parametric amplification in ultra-silicon-rich nitride (USRN) waveguides. , 2018, , .		0
72	Telecom InAs quantum-dot FP and microdisk lasers epitaxially grown on (111)-faceted SOI. , 2020, , .		0

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73	1300 nm and 1500 nm InAs/GaAs quantum dot lasers directly grown on SOI substrates for silicon photonics integration. , 2021, , .		0
74	O-band P-doped InAs/GaAs quantum dot lasers directly grown on SOI substrate. , 2021, , .		0